

Notice of References Cited	Application/Control No. 10/612,941		Applicant(s)/Patent Under Reexamination YOON, DONG-SOO	
	Examiner Lisa A Kilday		Art Unit 2829	Page 1 of 1

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	M	US-			

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NON-PATENT DOCUMENTS

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	U	Zhan et al., "Characteristics of High Quality Hafnium oxide Gate dielectric", Electron Devices Meeting, 2002., IEEE Hong Kong, 22 June 2002, pp. 43-46
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.